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1. Global joint venture starts operations as WeEn Semiconductors

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As from November 9th, 2015 NXP Semiconductors N.V. and Beijing JianGuang Asset Management Co. Ltd established Bipolar Power joint venture (JV), **WeEn Semiconductors**, which will be used in future Bipolar Power documents together with new contact details.

In this document where the previous NXP references remain, please use the new links as shown below.

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Thank you for your cooperation and understanding,

WeEn Semiconductors



Product data sheet

Product profile

1.1 General description

Hyperfast, epitaxial rectifier diode in a SOD113 (2-lead TO-220F) plastic package.

1.2 Features

- Extremely fast switching
- Low reverse recovery current
- Reduces switching loss in associated **MOSFET**
- Low thermal resistance
- Isolated package

1.3 Applications

- Half-bridge or full-bridge switched-mode Continuous Current Mode (CCM) Power power supplies
- Half-bridge lighting ballasts
- Factor Correction (PFC)

1.4 Quick reference data

- V_{RRM} ≤ 600 V
- $V_F = 1.54 \text{ V (typ)}$

- $I_{F(AV)} \le 20 A$
- $t_{rr} = 19 \text{ ns (typ)}$

Pinning information 2.

Table 1. **Pinning**

Pin	Description	Simplified outline	Symbol
1	cathode (k)		. 14
2	anode (a)	mb	k — a 001aaa020
mb	mounting base; isolated		
		SOD113 (2-lead TO-220	OF)



Ordering information

Table 2. **Ordering information**

Type number	Package					
	Name	Description	Version			
BYC20X-600	TO-220F	plastic single-ended package; isolated heatsink mounted; 1 mounting hole; 2-lead TO-220 'full pack'	SOD113			

Limiting values 4.

Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{RRM}	repetitive peak reverse voltage		-	600	V
V_{RWM}	crest working reverse voltage		-	600	V
V_R	reverse voltage	square waveform; δ = 1.0; $T_h \le 100$ °C	-	500	V
I _{F(AV)}	average forward current	square waveform; δ = 0.5; $T_h \le$ 25 °C	-	20	Α
I _{FRM}	repetitive peak forward current	square waveform; δ = 0.5; $T_h \le$ 25 °C; t_p = 25 μs	-	40	Α
I _{FSM}	non-repetitive peak forward	t = 10 ms; sinusoidal waveform	-	250	Α
	current	t = 8.3 ms; sinusoidal waveform	-	274	Α
T _{stg}	storage temperature		-40	+150	°C
T _i	junction temperature		-	150	°C

5. Thermal characteristics

Table 4. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-h)}$	thermal resistance from junction to heatsink	with heatsink compound; see Figure 1	-	-	2.6	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	in free air	-	55	-	K/W

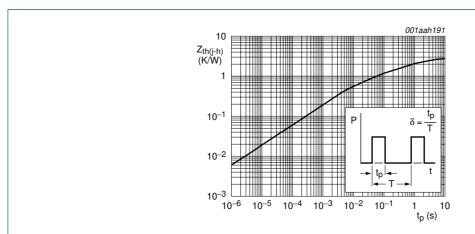


Fig 1. Transient thermal impedance from junction to heatsink as a function of pulse width

6. Isolation characteristics

Table 5. Isolation limiting values and characteristics

 $T_h = 25 \,^{\circ}C$ unless otherwise specified.

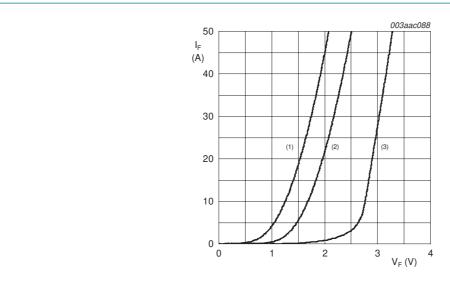
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{\text{isol}(\text{RMS})}$	RMS isolation voltage	from all terminals to external heatsink; $f = 50$ Hz to 60 Hz; sinusoidal waveform; relative humidity ≤ 65 %; clean and dust free	-	-	2500	V
C _{isol}	isolation capacitance	from pin 1 (cathode) to external heatsink; f = 1 MHz	-	10	-	pF

7. Characteristics

Table 6. Characteristics

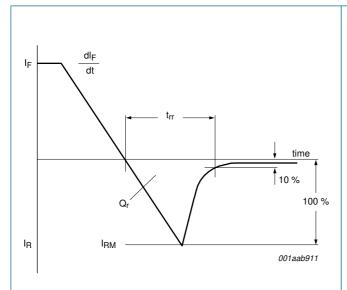
 $T_j = 25 \,^{\circ}C$ unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static char	racteristics					
V_{F}	forward voltage	$I_F = 20 \text{ A}$; $T_j = 150 ^{\circ}\text{C}$; see Figure 2	-	1.54	1.97	V
		$I_F = 40 \text{ A}; T_j = 150 ^{\circ}\text{C}; \text{see } \frac{\text{Figure 2}}{}$	-	1.95	2.34	V
		I _F = 20 A; see Figure 2	-	1.89	2.9	V
I _R	reverse current	V _R = 600 V	-	16	200	μΑ
		$V_R = 500 \text{ V}; T_j = 100 ^{\circ}\text{C}$	-	1.6	3.0	mA
Dynamic c	haracteristics					
t _{rr}	reverse recovery time	I_F = 1 A to V_R = 30 V; dI_F/dt = 50 A/ μ s; see Figure 3	-	35	55	ns
		I_F = 20 A to V_R = 400 V; dI_F/dt = 500 A/ μ s; see Figure 3				
		T _j = 25 °C	-	19	-	ns
		T _j = 100 °C	-	32	40	ns
I _{RM}	peak reverse recovery current	I_F = 20 A to V_R = 400 V; T_j = 125 °C; see Figure 3				
		$dI_F/dt = 50 A/\mu s$	-	3.0	7.5	Α
		$dI_F/dt = 500 A/\mu s$	-	9.5	12	Α
V_{FR}	forward recovery voltage	$I_F = 20 \text{ A}$; $dI_F/dt = 100 \text{ A/}\mu\text{s}$; see Figure 4	-	8	11	V



- (1) $T_j = 150 \,^{\circ}\text{C}$; typical values
- (2) $T_j = 150 \,^{\circ}C$; maximum values
- (3) $T_j = 25$ °C; maximum values

Fig 2. Forward current as a function of forward voltage



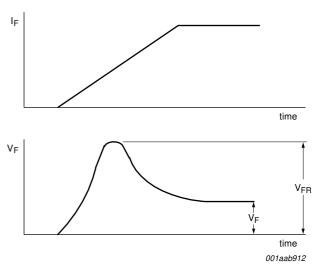


Fig 3. Reverse recovery definitions

Fig 4. Forward recovery definitions

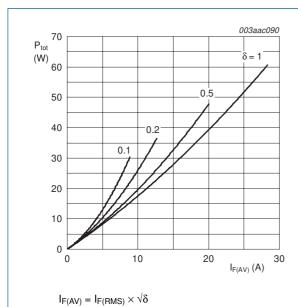
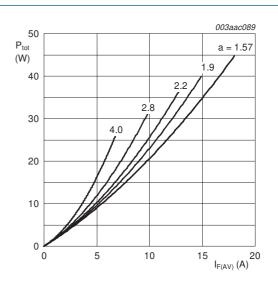


Fig 5. Forward power dissipation as a function of average forward current; square waveform; maximum values



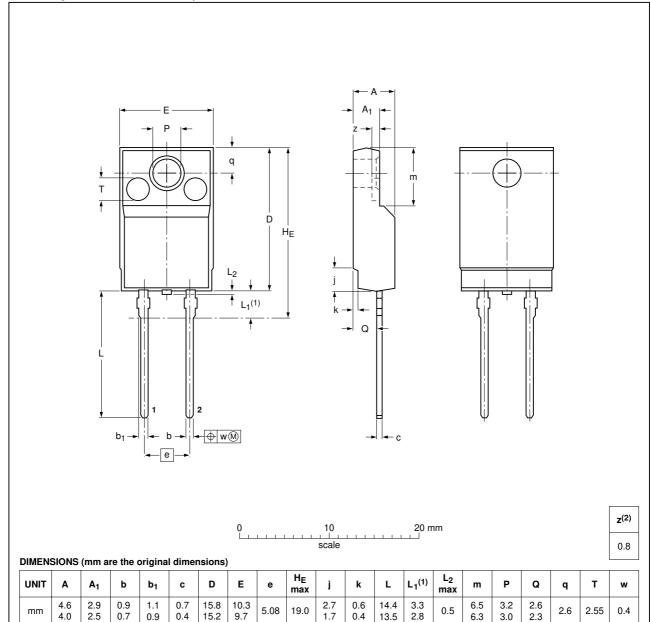
 $a = form \ factor = I_{F(RMS)} \ / \ I_{F(AV)}$

Fig 6. Forward power dissipation as a function of average forward current; sinusoidal waveform; maximum values

8. Package outline

Plastic single-ended package; isolated heatsink mounted; 1 mounting hole; 2-lead TO-220 'full pack'

SOD113



Notes

1. Terminals are uncontrolled within zone L₁.

2. z is depth of T.

OUTLINE		REFER	ENCES	EUROPEAN ISSUE	
VERSION	IEC	JEDEC	JEITA	PROJECTION	ISSUE DATE
SOD113		2-lead TO-220F			02-04-09 07-06-18

Fig 7. Package outline SOD113 (2-lead TO-220F)



9. Revision history

Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BYC20X-600_1	20071129	Product data sheet	-	-

10. Legal information

10.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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